

SEMICONDUCTOR®

FQP9N30

N-Channel QFET[®] MOSFET 300 V, 9.0 A, 450 mΩ

Description

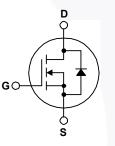
This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

GDS

Features

- + 9.0 A, 300 V, $R_{DS(on)}$ = 450 m Ω (Max.) @ V_{GS} = 10 V, I_{D} = 4.5 A
- Low Gate Charge (Typ. 17 nC)
- Low Crss (Typ. 16 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

Symbol	Parameter		FQP9N30	Unit
V _{DSS}	Drain-Source Voltage		300	V
I _D	Drain Current - Continuous (T _C = 25°	C)	9.0	A
	- Continuous (T _C = 100)°C)	5.7	A
DM	Drain Current - Pulsed	(Note 1)	36	A
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	420	mJ
I _{AR}	Avalanche Current	(Note 1)	9.0	A
E _{AR}	Repetitive Avalanche Energy	(Note 1)	9.8	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns
P _D	Power Dissipation (T _C = 25°C)		98	W
	- Derate above 25°C		0.78	W/°C
T _J , T _{STG}	Operating and Storage Temperature Ran	nge	-55 to +150	°C
TL	Maximum Lead Temperature for Solderir 1/8" from Case for 5 seconds	ng,	300	°C

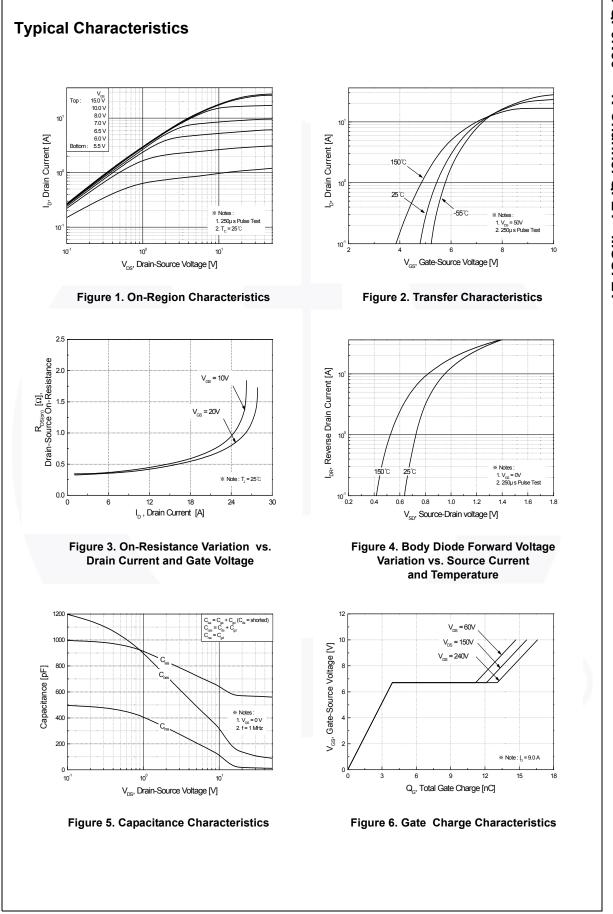
Thermal Characteristics

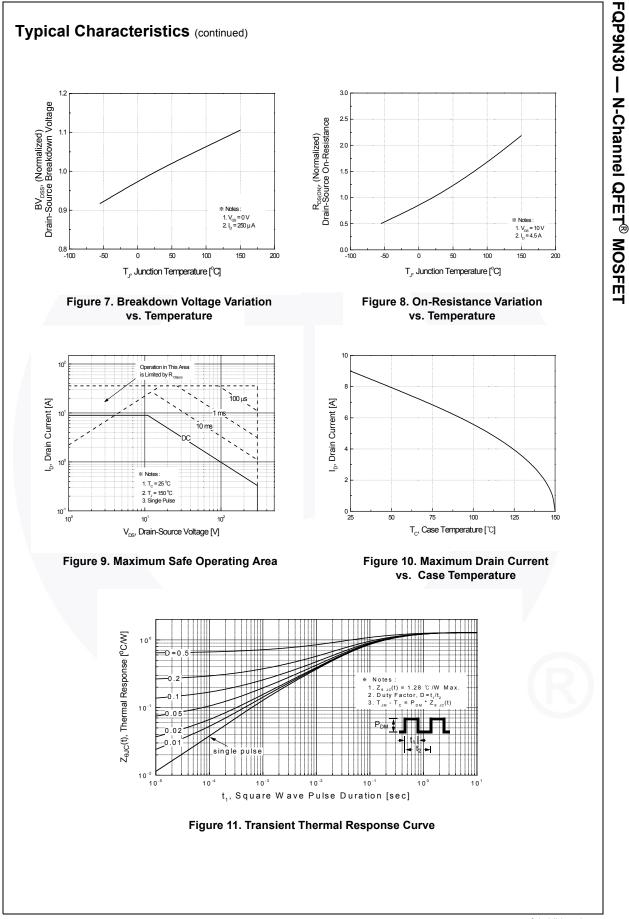
Symbol	Parameter	FQP9N30	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	1.28	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

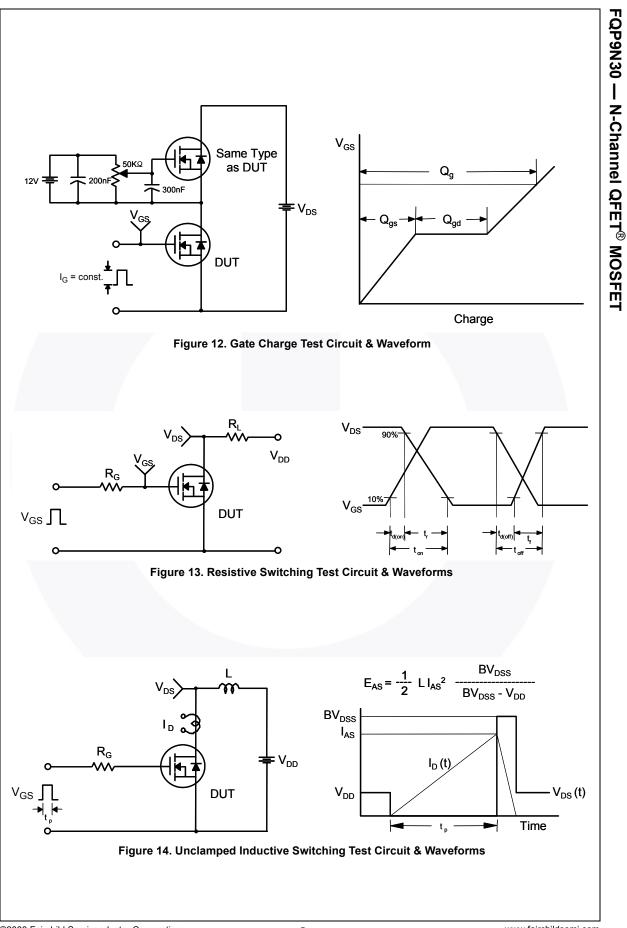
November 2013

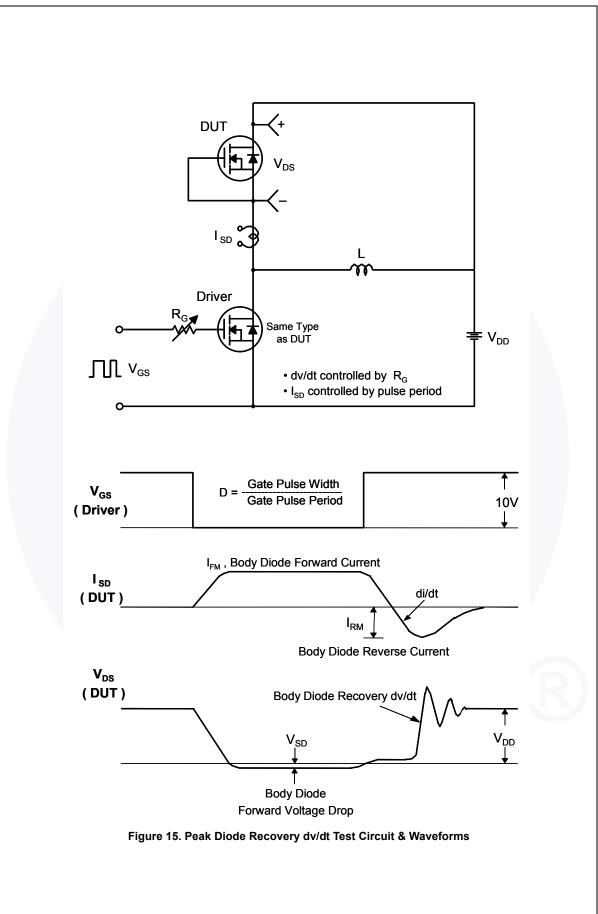
Part NumberTop MarkPackageFQP9N30FQP9N30TO-220		Package	Packing Method	Reel Size	Tape Width		th Q	Quantity	
		Tube N/A		N/A		5	50 units		
lectri	cal C	haracteristics	T _C = 25°C	unless otherwise noted.					
Symbol		Parameter		Test Condit	ions	Min	Тур	Max	Unit
Off Cha	aracto	rietice							
BV _{DSS}	1	Source Breakdown V	oltage	V _{GS} = 0 V, I _D = 250 µ	ιA	300			V
ABV _{DSS}	Breakdown Voltage Temperature Coefficient		$I_D = 250 \ \mu$ A, Referenced to 25°C					-	
ΔT_J						0.28		V/°C	
DSS	Zero Gate Voltage Drain Current			V_{DS} = 300 V, V_{GS} = 0) V			1	μA
			V _{DS} = 240 V, T _C = 125°C				10	μA	
GSSF	Gate-	Body Leakage Currer	t, Forward	V _{GS} = 30 V, V _{DS} = 0 V				100	nA
GSSR	Gate-Body Leakage Current, Reverse		it, Reverse	V_{GS} = -30 V, V_{DS} = 0 V				-100	nA
On Cha	ractor	istics							
V _{GS(th)}		Threshold Voltage		V _{DS} = V _{GS} , I _D = 250	uА	3.0		5.0	V
R _{DS(on)}		Drain-Source		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 4.5$			0.35	0.45	-
	On-Re	esistance					0.55	0.45	Ω
ØFS	Forwa	rd Transconductance		$V_{\rm DS}$ = 50 V, $I_{\rm D}$ = 4.5	A		4.9		S
Dvnam	ic Cha	racteristics							
C _{iss}	Input Capacitance						570	740	pF
C _{oss}	· · ·	t Capacitance		V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz			120	155	pF
Crss	· · ·	se Transfer Capacita	nce				16	20	pF
Switch	ing Ch	aracteristics						1	
d(on)	Turn-C	On Delay Time		V _{DD} = 150 V, I _D = 9.0 A,			16	40	ns
r	Turn-C	On Rise Time		$R_G = 25 \Omega$,		120	250	ns
d(off)	Turn-C	Off Delay Time		0			27	65	ns
f	Turn-C	Off Fall Time			(Note 4)		48	110	ns
ζ ^g	Total C	Sate Charge		V _{DS} = 240 V, I _D = 9.0) A,		17	22	nC
2 _{gs}	Gate-S	Source Charge		$V_{GS} = 10 V$ (Note 4)			3.9		nC
2 _{gd}	Gate-I	Drain Charge					9.2		nC
				d Maximum Rati	ngs			0.0	۸
S		um Continuous Drain						9.0	A
SM		ium Pulsed Drain-So	1					36	A
/ _{SD}		Source Diode Forwar	u voitage	$V_{GS} = 0 \text{ V, } I_S = 9.0 \text{ A}$ $V_{GS} = 0 \text{ V, } I_S = 9.0 \text{ A,}$ $dI_F / dt = 100 \text{ A}/\mu\text{s}$				1.5	V
m C		se Recovery Time					170		ns
ל ^{ער}	Reven	se Recovery Charge					1.4		μC

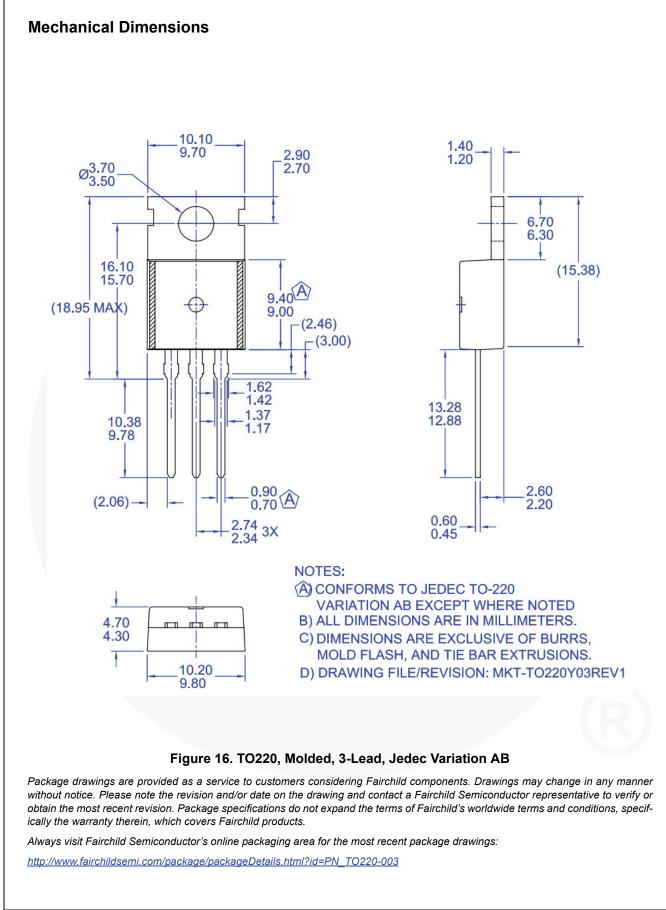
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